

# NVTF5010N10MCL

## MOSFET - Power, Single N-Channel

### 100 V, 10.6 mΩ, 57.8 A

#### Features

- Small Footprint (3.3 x 3.3 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- NVTF5010N10MCLTAG – Wettable Flanks Product
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	$V_{DS}$	100	V	
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V	
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3)	Steady State	$T_C = 25^\circ\text{C}$	57.8	A
		$T_C = 100^\circ\text{C}$	40.8	
Power Dissipation $R_{\theta JC}$ (Notes 1, 2)	Steady State	$T_C = 25^\circ\text{C}$	77.8	W
		$T_C = 100^\circ\text{C}$	38.9	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	11.7	A
		$T_A = 100^\circ\text{C}$	8.3	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	3.2	W
		$T_A = 100^\circ\text{C}$	1.6	
Pulsed Drain Current	$T_C = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	$I_{DM}$	232	A
Source Current	$I_S$	64.8	A	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$	
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 2.9 \text{ A}$ )	$E_{AS}$	526	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 2)	$R_{\theta JC}$	1.93	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	46.6	

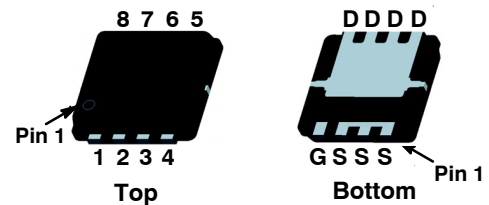
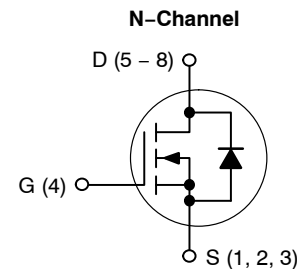
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



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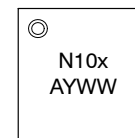
[www.onsemi.com](http://www.onsemi.com)

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
100 V	10.6 mΩ @ 10 V	57.8 A
	15.9 mΩ @ 4.5 V	



WDFN8  
(3.3x3.3, 0.65 P)  
CASE 511DY

#### MARKING DIAGRAM



N10x = Specific Device Code  
x = L or W  
A = Assembly Location  
Y = Year Code  
WW = Work Week Code

#### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# NVTFS010N10MCL

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>			64		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 80 V	T <sub>J</sub> = 25°C		1.0	μA
			T <sub>J</sub> = 125°C		250	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V			100	nA

### ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 85 μA	1.0	1.5	3.0	V	
Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>			-5.3		mV/°C	
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A		9.1	10.6	mΩ
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 12 A		13.5	15.9	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 15 A		54		S	

### CHARGES AND CAPACITANCES

Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 50 V		1530	2150	pF
Output Capacitance	C <sub>OSS</sub>			625	875	
Reverse Transfer Capacitance	C <sub>RSS</sub>			10	18	
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 50 V; I <sub>D</sub> = 15 A		10		nC
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 50 V; I <sub>D</sub> = 15 A		22	30	
Gate-to-Source Charge	Q <sub>GS</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 50 V; I <sub>D</sub> = 15 A		4.0		nC
Gate-to-Drain Charge	Q <sub>GD</sub>			3.0		

### SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 50 V, I <sub>D</sub> = 15 A, R <sub>G</sub> = 6 Ω		9.0		ns
Rise Time	t <sub>r</sub>			3.0		
Turn-Off Delay Time	t <sub>d(OFF)</sub>			28		
Fall Time	t <sub>f</sub>			5.0		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 15 A		0.8	1.3	V
Reverse Recovery Time	t <sub>RR</sub>	I <sub>F</sub> = 8 A, di/dt = 300 A/μs		22	36	ns
Reverse Recovery Charge	Q <sub>RR</sub>			35	56	nC
Reverse Recovery Time	t <sub>RR</sub>	I <sub>F</sub> = 8 A, di/dt = 1000 A/μs		17	30	ns
Reverse Recovery Charge	Q <sub>RR</sub>			79	126	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperatures.

# NVTF5010N10MCL

## TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

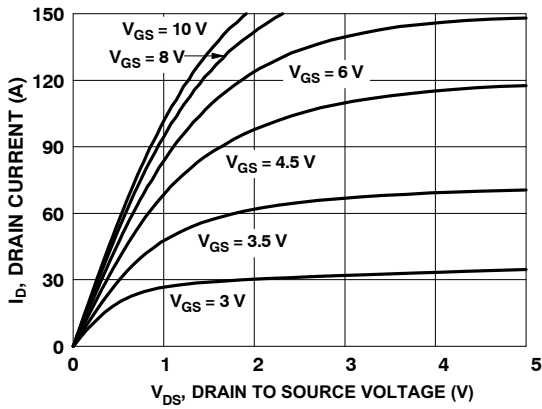


Figure 1. On Region Characteristics

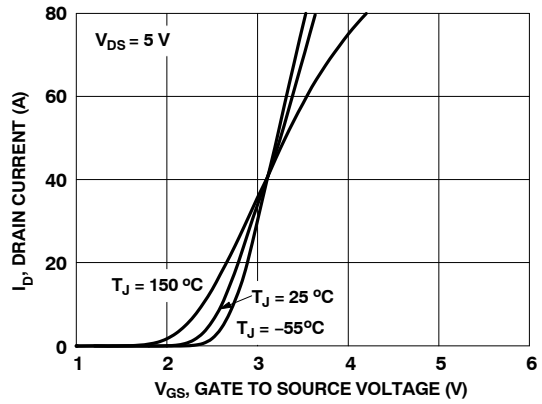


Figure 2. Transfer Characteristics

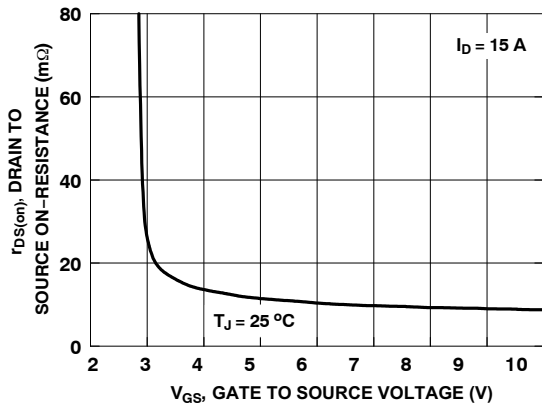


Figure 3. On-Resistance vs. Gate to Source Voltage

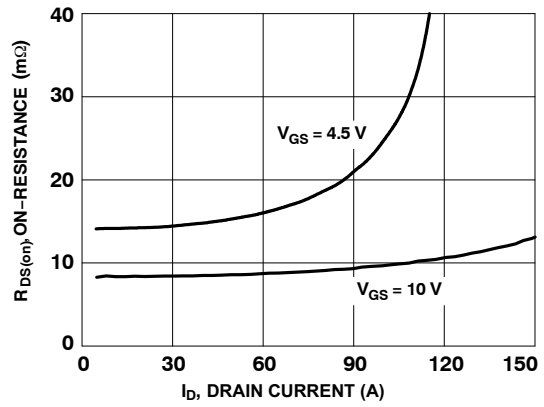


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

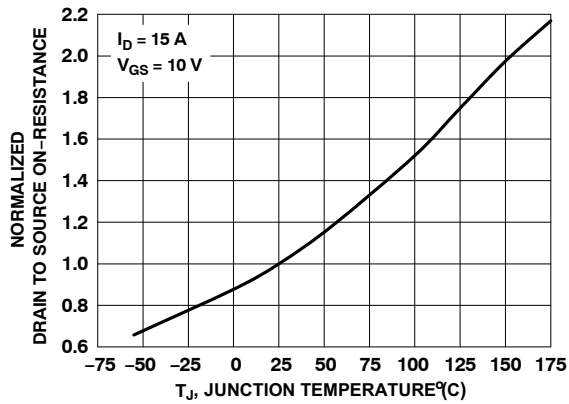


Figure 5. Normalized On Resistance vs. Junction Temperature

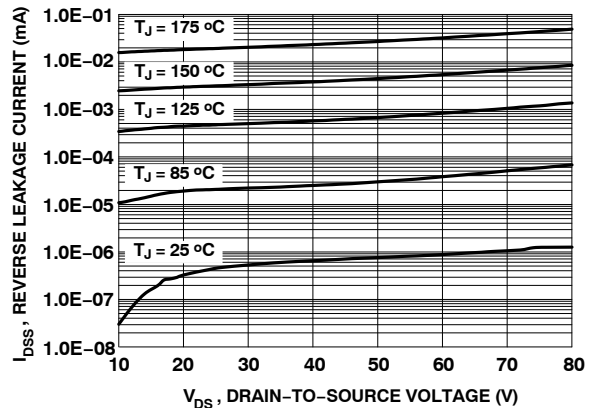


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NVTFS010N10MCL

## TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

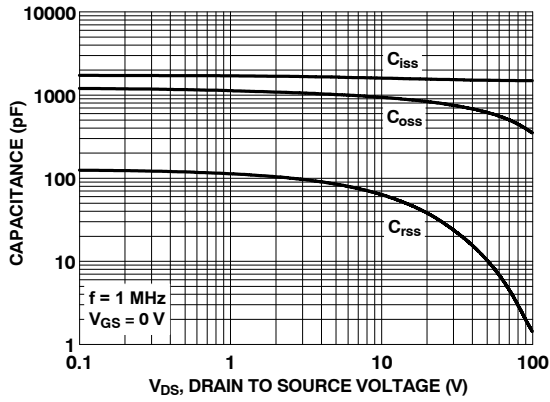


Figure 7. Capacitance vs. Drain to Source Voltage

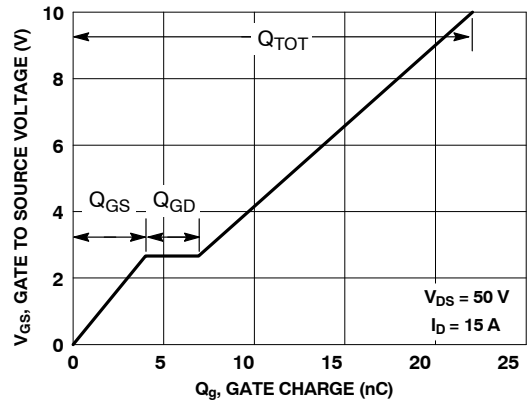


Figure 8. Gate Charge Characteristics

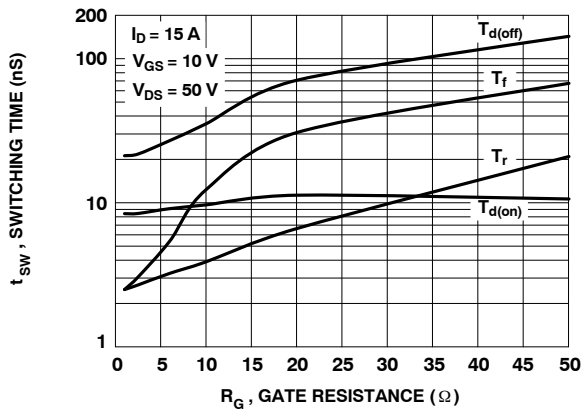


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

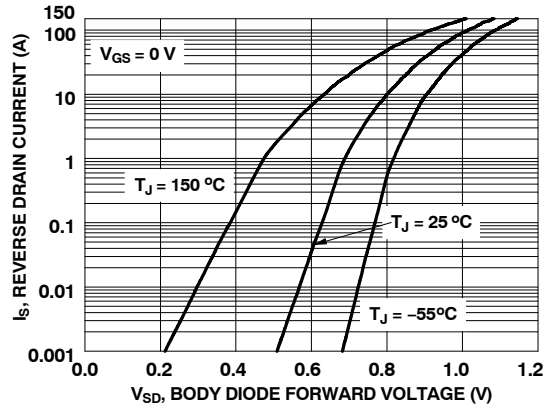


Figure 10. Source to Drain Diode Forward Voltage vs. Source Current

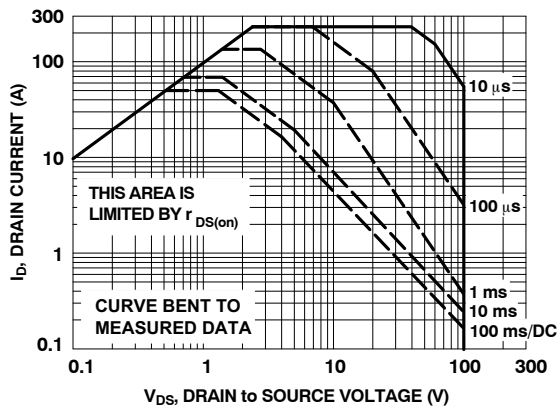


Figure 11. Forward Bias Safe Operating Area

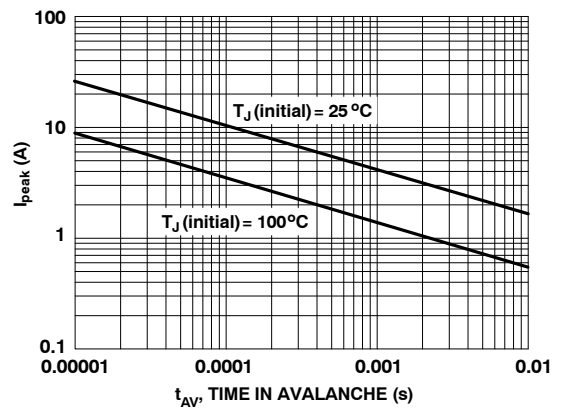


Figure 12. Unclamped Inductive Switching Capability

# NVTFS010N10MCL

## TYPICAL CHARACTERISTICS (continued)

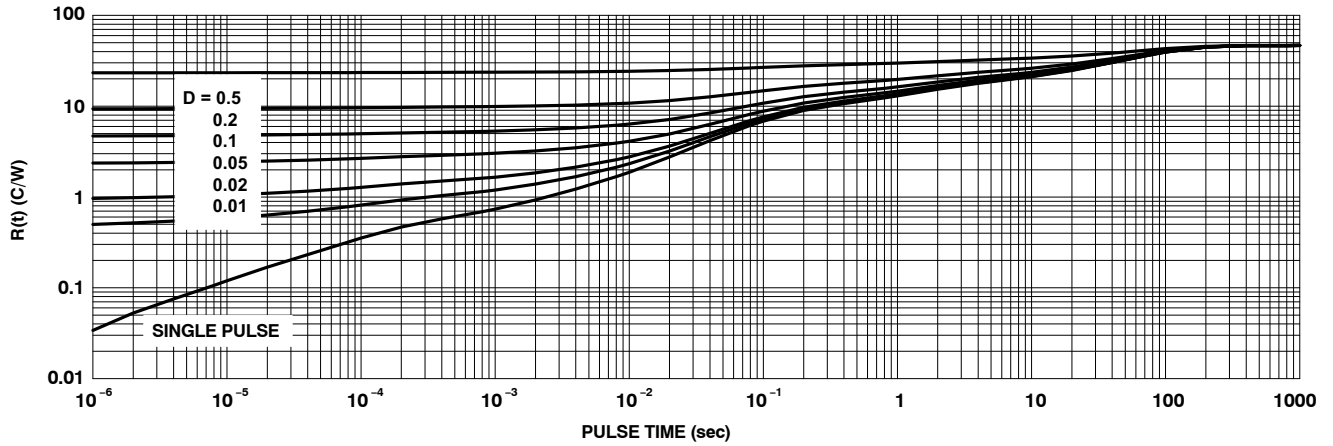


Figure 13. Junction-to-Case Transient Thermal Response Curve

### DEVICE ORDERING INFORMATION

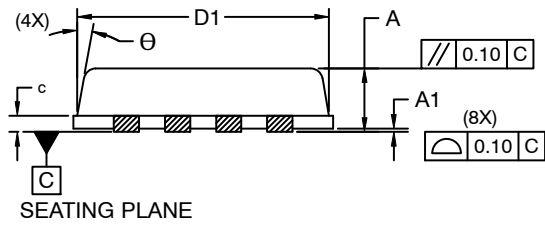
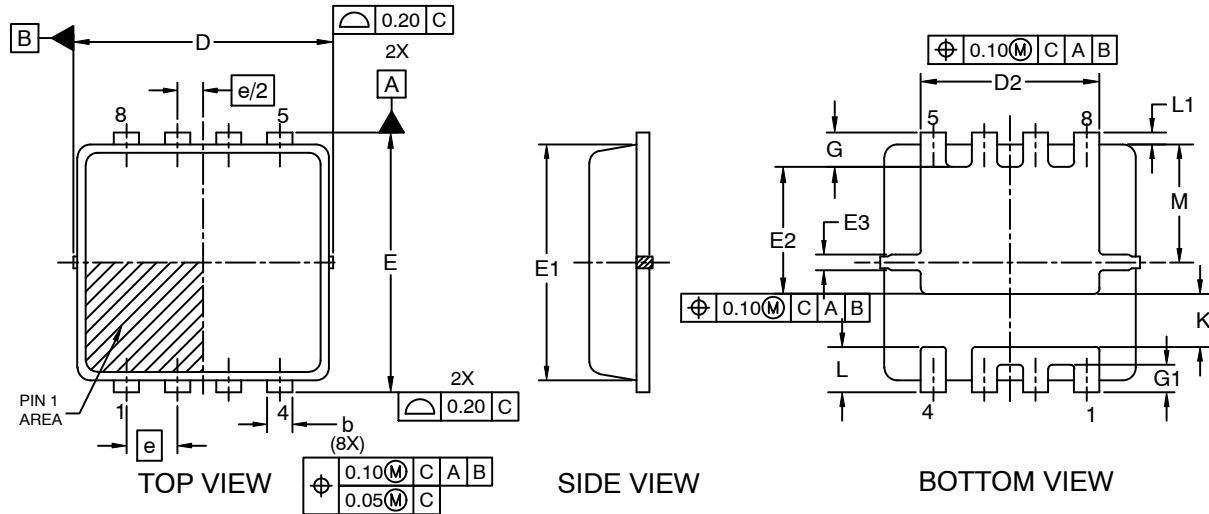
Device	Marking	Package	Shipping <sup>†</sup>
NVTFS010N10MCLTAG	N10L	WDFN8 (Pb-Free)	1500 / Tape & Reel
NVTFWS010N10MCLTAG	N10W	WDFN8 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

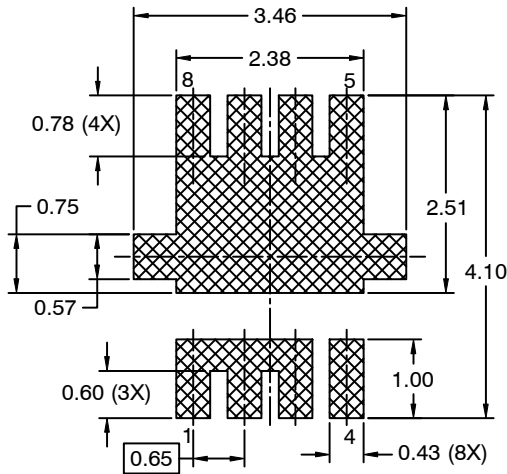
# NVTF010N10MCL

## PACKAGE DIMENSIONS

WDFN8 3.3x3.3, 0.65P  
CASE 511DY  
ISSUE A



END VIEW




RECOMMENDED LAND PATTERN

**NOTES:**

1. CONTROLLING DIMENSION: MILLIMETERS
2. DIMENSIONS D1 & E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS NOR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	-	0.05
b	0.23	0.33	0.43
c	0.15	0.20	0.25
D	3.20	3.30	3.40
D1	2.95	3.13	3.30
D2	1.98	2.20	2.40
E	3.20	3.30	3.40
E1	2.80	3.00	3.15
E2	1.40	1.60	1.80
E3	0.15	0.25	0.40
e	0.65 BSC		
G	0.30	0.43	0.55
G1	0.25	0.35	0.45
K	0.55	0.75	0.95
L	0.35	0.52	0.65
L1	0.06	0.15	0.30
M	1.35	1.50	1.60
θ	0	-	12

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